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Sommario/riassunto	Gallium Oxide: Technology, Devices and Applications discusses the wide bandgap semiconductor and its promising applications in power electronics, solar blind UV detectors, and in extreme environment electronics. It also covers the fundamental science of gallium oxide, providing an in-depth look at the most relevant properties of this materials system. High quality bulk Ga2O3 is now commercially available from several sources and n-type epi structures are also coming onto the market. As researchers are focused on creating new complex structures, the book addresses the latest processing and synthesis methods. Chapters are designed to give readers a complete picture of the Ga2O3 field and the area of devices based on Ga2O3, from their theoretical simulation, to fabrication and application.